



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

SS26L

SMA Schottky Barrier Rectifier Diode 肖特基势垒整流二极管

■Features 特点

Low forward voltage drop 低正向压降

High current capability 高电流能力

Surface mount device 表面贴装器件

Case 封装:SMA(DO-214AC)



■Maximum Rating 最大额定值

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	SS26L	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	60	V
DC Reverse Voltage 直流反向电压	V_R	60	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	42	V
Forward Rectified Current 正向整流电流	I_F	2	A
Peak Surge Current 峰值浪涌电流	I_{FSM}	50	A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	88	$^{\circ}\text{C}/\text{W}$
Junction Temperature 结温	T_J	125	$^{\circ}\text{C}$
Storage Temperature 储藏温度	T_{stg}	$-55\text{to}+150^{\circ}\text{C}$	$^{\circ}\text{C}$

■Electrical Characteristics 电特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	SS26L	Unit 单位	Condition 条件
Forward Voltage 正向电压	V_F	0.55	V	$I_F=2\text{A}$
Reverse Current 反向电流	$I_R(25^{\circ}\text{C})$ (125°C)	0.15 30	mA	$V_R=V_{RRM}$
Diode Capacitance 二极管电容	C_D	170	pF	$V_R=4\text{V}, f=1\text{MHz}$

■ Typical Characteristic Curve 典型特性曲线

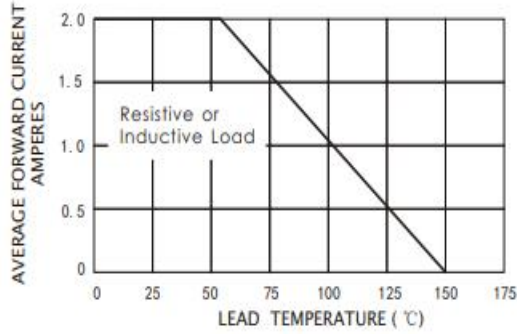


Figure 1: Forward Current Curve

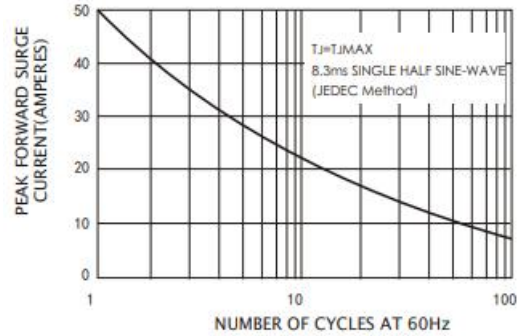


Figure 2: Forward Surge Current Curve

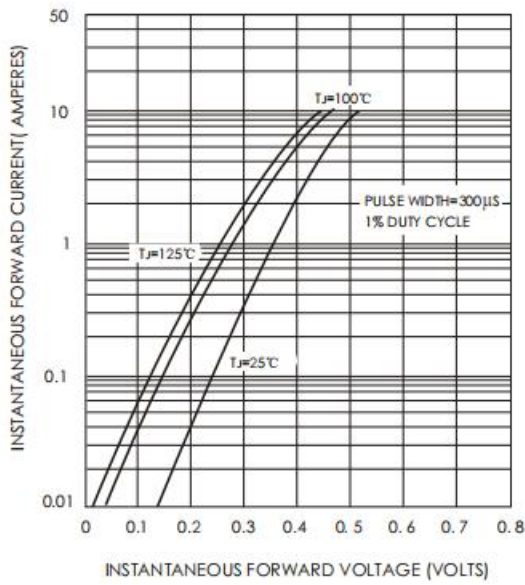


Figure 3: Forward Characteristics

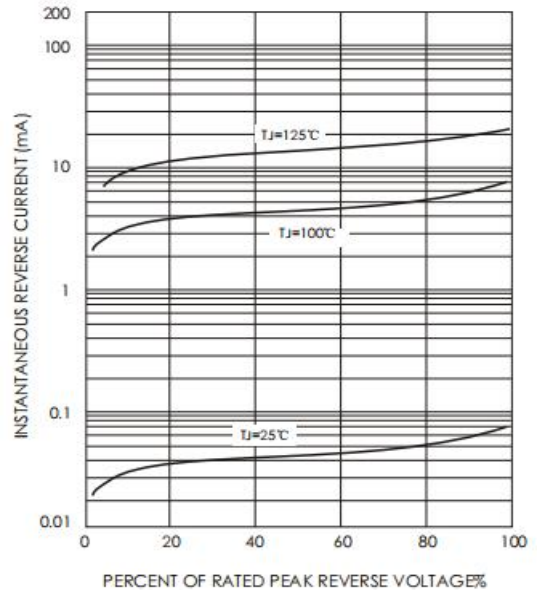


Figure 4: Reverse Characteristics

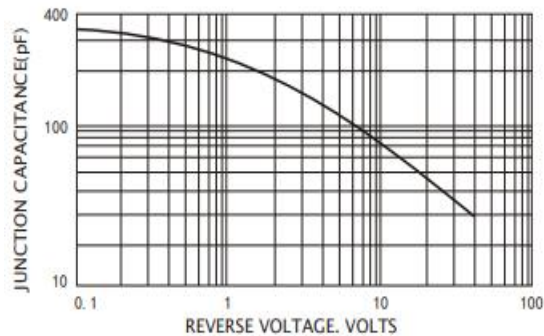
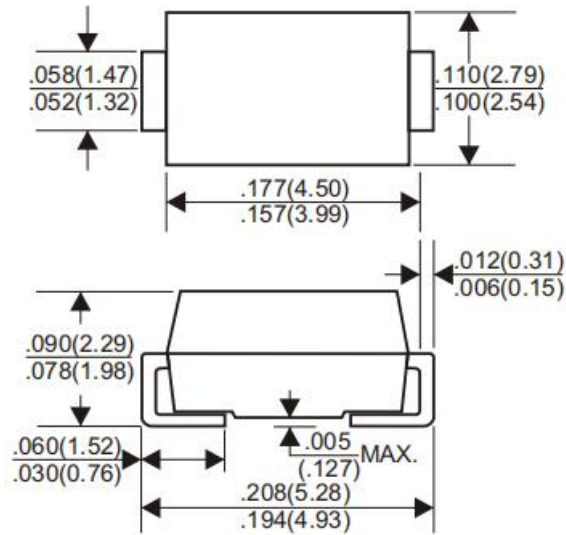


Figure 5: Capacitance Characteristics

■Dimension 外形封装尺寸

DO-214AC(SMA)



Dimensions in inches and (millimeters)